제20회 한국반도체학술대회

2013년 2월 4일(월)~6일(수) / 웰리힐리파크 (구, 성우리조트)

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G. Device & Process Modeling, Simulation and Reliability 분과

Room H

난실 (본관, 5층)

2013년 2월 6일(수) 15:10-16:25

[WH3-G] Device Reliability

좌장: 이상기(동부하이텍), 최재훈(SK 하이닉스)

WH3-G-1 **15:10-15:25**

Effects of Ionizing Radiation on Undoped Double-Gate FinFETs
Jungsik Nam[1], Chang Yong Kang[2], KwangPyo Kim[3], Boung Jun Lee[1], and Ji-Woon Yang[1]
[1]Department of Electronics & Information Engineering, Korea University, [2]Front-End Process Division, SEMATECH, Inc., [3]Department of Nuclear Engineering, Kyung Hee University

WH3-G-2 **15:25-15:40**

Different Negative Bias Illumination Stabilities according to the Zn/Sn Atomic Compositions in Zinc Tin Oxide Thin Film Transistors
Un Ki Kim[1], Sang Ho Rha[1], Jeong Hwan Kim[1], Yoon Jang Chung[1], Jisim Jung[1], Eun Suk Hwang[1], Tae joo Park[2], and Cheol Seong Hwang[1]
[1]Department of Materials Science and Engineering, WCU Hybrid Materials Program and Inter-University Semiconductor Research Center, Seoul National University, [2]Department of Materials Science and Engineering, Hanyang University

WH3-G-3 **15:40-15:55**

Design of Halo-Doped LDD NMOSFETs Robust to Hot-Carrier Stress for Source Driver Applications
Yon-Sup Pang, Sookjin Kwon, Gukhwan Kim, Youngju Kim, Leeyeun Hwang, Boseok Oh, Sung-Bum Park, and Taejong Lee
Device Infra and HV Teams, Corporate Engineering, MagnaChip Semiconductor

WH3-G-4 **15:55-16:10**

Characterization of Negative Bias Stress Instability Mechanisms in Amorphous InGaZnO Thin Film Transistors
Chunhyung Jo, Sungwoo Jun, Woojoon Kim, Inseok Hur, Jaeman Jang, Jaehyeong Kim, Jaewook Lee, Yun Hyeok Kim, Hagyoul Bae, Dong Jae Shin, Kyung Min Lee, Hyeongjung Kim, Dae Hwan Kim, and Dong Myong Kim
School of Electrical Engineering, Kookmin University

WH3-G-5 **16:10-16:25**

The Vibration Reliability Analysis Considering the Board Level in a Memory Module
Chanhee Seo[1], Yinghu Xu[1], Jaeseok Jang[1], Jungjoon Lee[1], Yusuf Cinar[2], Kyoungwon Seo[2], and Gunhee Jang[2]
[1]Samsung Electronics Memory business
[2]Department of Mechanical Engineering, Hanyang University